

#7B Amolt 5Dains 9/4/02

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

Ende SHAN, et al.

: EXAMINER: TOLEDO, F.

SERIAL NO.: 09/688,817

: GROUP ART UNIT: 2823

FILED: OCTOBER 17, 2000 '

FOR: LOW TEMPERATURE

METALLIZATION PROCESS

RECEIVED 1967 2800 TECHNOLOGY CENTER 2800

AMENDMENT AND REQUEST FOR RECONSIDERATION

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

In response to the Official Action of February 14, 2002, reconsideration of the aboveidentified application is respectfully requested in view of the following amendment and remarks.

IN THE CLAIMS

Please amend the claims to read as follows:

- 1. (Twice Amended) A method of forming a layer of metal on a substrate, comprising:
- i) depositing a seed layer of the metal on a first substrate surface which is Ti, said seed layer being sufficient to cover said first substrate surface which is Ti at a substrate temperature of from 220 to 300°C;